Session Code [09] MoJ3

Session Title Power / Oxide Semiconductor Materials and Devices
Date and Time Monday, October 4, 2021 / 15:30-16:40
Session Room Room J (401)
Session Chair(s) Daesu Lee (POSTECH, Korea)

[[09] MoJ3-1] [Online] 15:30-15:45
Characterization of X-Ray Radiation Hardness of Diamond Schottky Barrier Diodes up to 10 MGy
Phongsaphak Sittimart, Shinya Ohmagari, Tomoki Iwao, Hitoshi Umezawa (Nat’l Inst. of Advanced Industrial Sci. and Tech., Japan), Katoro Ishiji (Kyushu Synchrotron Light Research Center, Japan), and Tsuyoshi Yoshitake (Kyushu Univ., Japan)

[[09] MoJ3-2] [Online] 15:45-16:00
Zn-Doped p-Type β-Ga2O3: Ultra-High Critical Electric Field
Ekaterine Chikoidze (Univ. Paris-Saclay, France and CNRS, France), Tamar Tchelidze (Ivane Javakhishvili Tbilisi State Univ., Georgia), Corinne Sartel, Zeyu Chi (Univ. Paris-Saclay, France and CNRS, France), Riad Kabouche (IEMN, CNRS, France), Ismail Madaci (Univ. Paris-Saclay, France and CNRS, France), Carles Rubio (ICN2, Spain), Hagar Mohamed, Vincent Sallet (Univ. Paris-Saclay, France and CNRS, France), Farid Medjdoub (IEMN, CNRS, France), and Yves Dumont (Univ. Paris-Saclay, France and CNRS, France)

[[09] MoJ3-3] 16:00-16:15
Advanced Thermal Interface Material with High Thermal Conductivity for High Power Devices
MiKyeong Choi (Amkor Tech. Inc., Korea and Sungkyunkwan Univ., Korea), HyunHye Jung, DongJoo Park, JinYoung Khim (Amkor Tech. Inc., Korea), and SeungBoo Jung (Sungkyunkwan Univ., Korea)

Enhancing Dielectric Constant of ZnO by Acceptor-Donor Co-Doping
Chi-Chung Francis Ling, Dong Huang, Yingli Shi (The Univ. of Hong Kong, Hong Kong), Shengqiang Zhou (Helmholtz-Zentrum Dresden-Rossendorf, Germany), and Andrej Kuznetsov (Univ. of Oslo, Norway)